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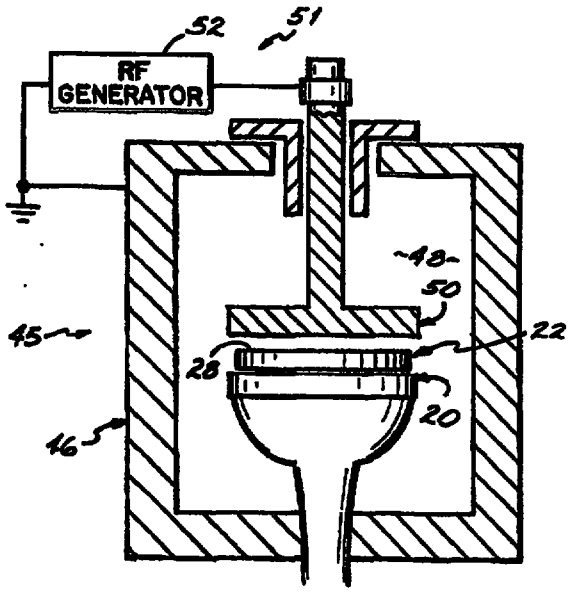
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(54) Title: METHOD OF ELIMINATING EDGE EFFECT IN CHEMICAL VAPOR DEPOSITION OF A METAL



(57) Abstract

A method of eliminating an edge effect in chemical vapor deposition of a metal such as copper on a semiconductor substrate (22) surface (26a, 26b). A susceptor (20) in a reaction chamber (46) is exposed to a plasma. A substrate (22) contained thereon and processed by chemical vapor deposition has a uniform metal layer at edge (44) and non–edge surfaces (28). A plurality of substrates (22) may be processed before reexposing the susceptor (20) to the plasma.